

ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1, photoresist polymers thereof,
and photoresist compositions containing the same. The photoresist polymer includes
a repeating unit comprising the photoresist monomer of Formula 1 as a comonomer
5 and the photoresist composition containing the same have excellent etching resistance,
heat resistance and adhesiveness to a wafer, and is developable in aqueous
tetramethylammonium hydroxide (TMAH) solution. In addition, the photoresist
composition has low light absorbance at 157nm wavelength, and thus is suitable for a
photolithography process using ultraviolet light sources such as VUV (157nm) in
10 fabricating a minute circuit for a high integration semiconductor device.

Formula 1

